

BENHA UNIVERSITY FACULTY OF ENGINEERING AT SHOUBRA

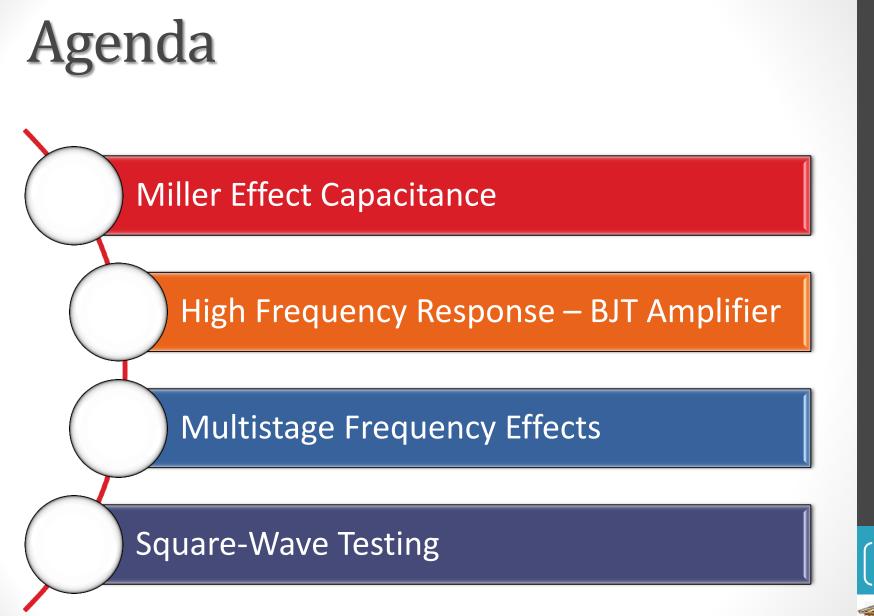
ECE-3 | 2 Electronic Circuit/ (A)

Lecture # 8 BJT High Frequency Response

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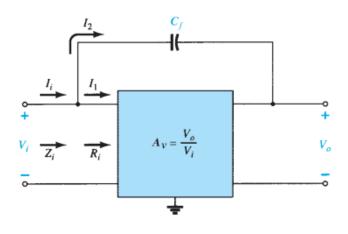
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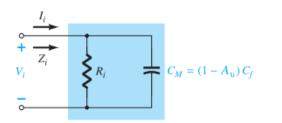
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Miller input capacitance $C_{M_i} = (1 - A_v)C_f$

- In the high-frequency region, the capacitive elements of importance are the interelectrode (between-terminals) capacitances internal to the active device and the wiring capacitance between leads of the network.
- For any inverting amplifier, the input capacitance will be increased by a Miller effect capacitance sensitive to the gain of the amplifier and the interelectrode (parasitic) capacitance between the input and output terminals of the active device.





Applying Kirchhoff's current law gives

$$I_i = I_1 + I_2$$

Using Ohm's law yields

$$I_{i} = \frac{V_{i}}{Z_{i}}, \quad I_{1} = \frac{V_{i}}{R_{i}}$$
$$I_{2} = \frac{V_{i} - V_{o}}{X_{C_{f}}} = \frac{V_{i} - A_{v}V_{i}}{X_{C_{f}}} = \frac{(1 - A_{v})V_{i}}{X_{C_{f}}}$$

 $\frac{V_i}{Z_i} = \frac{V_i}{R_i} + \frac{(1 - A_v)V_i}{X_{C_f}}$

 $\frac{1}{Z_i} = \frac{1}{R_i} + \frac{1}{X_{C_i}/(1 - A_v)}$

 $\frac{X_{C_f}}{1 - A_v} = \frac{1}{\omega(1 - A_v)C_f} = X_{C_M}$

 $\frac{1}{Z_i} = \frac{1}{R_i} + \frac{1}{X_{C_i}}$

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Substituting, we obtain

and

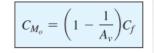
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but

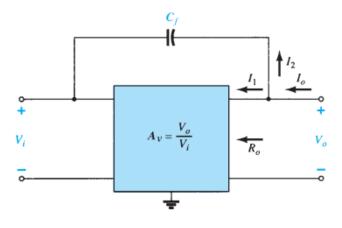
and



Miller output capacitance



- A positive value for A_v would result in a negative capacitance (for Av > 1).
- For noninverting amplifiers such as the common-base and emitter-follower configurations, the Miller effect capacitance is not a contributing concern for high-frequency applications.
- The Miller effect will also increase the level of output capacitance, which must also be considered when the high-frequency cutoff is determined.



$$I_o = I_1 + I_2$$

$$I_1 = \frac{V_o}{R_o} \quad \text{and} \quad I_2 = \frac{V_o - V_i}{X_{C_f}}$$

The resistance R_o is usually sufficiently large to permit ignoring the first term of the equation compared to the second term and assuming that

$$I_o \cong \frac{V_o - V_i}{X_{C_f}}$$

Substituting $V_i = V_o/A_v$ from $A_v = V_o/V_i$ results in

$$I_o = \frac{V_o - V_o/A_v}{X_{C_f}} = \frac{V_o(1 - 1/A_v)}{X_{C_f}}$$
$$\frac{I_o}{V_o} = \frac{1 - 1/A_v}{X_{C_f}}$$

 $\frac{V_o}{I_o} = \frac{X_{C_f}}{1 - 1/A_v} = \frac{1}{\omega C_f (1 - 1/A_v)} = \frac{1}{\omega C_{M_o}}$

and

or



 $C_{M_o} = \left(1 - \frac{1}{A}\right)C_f$

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5

HIGH FREQUENCY RESPONSE – BJT AMPLIFIER



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High Frequency Response

- At the high-frequency end, there are two factors that define the 3-dB cutoff point:
 - 1. the network capacitance (parasitic and introduced)
 - 2. the frequency dependence of h_{fe} (β).
- For RC circuit:

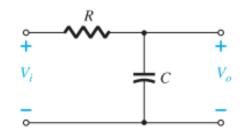
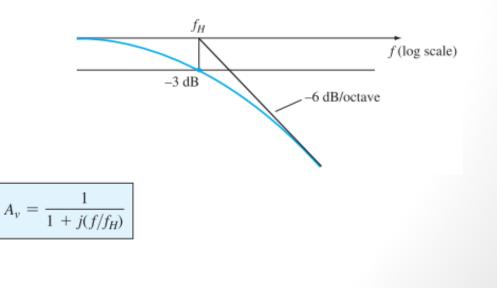


FIG. 9.45 RC combination that will define a high-cutoff frequency.



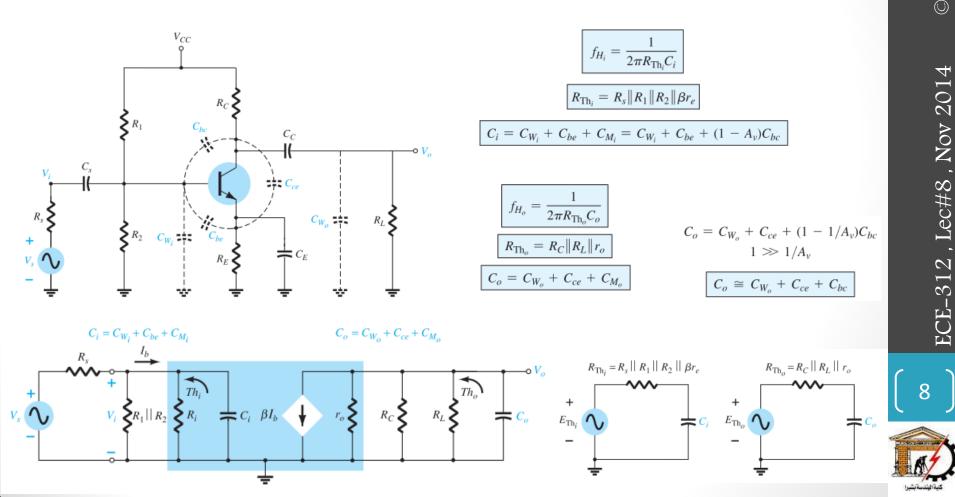




1. Network Parameters :

• At high frequencies, the various parasitic capacitances (C_{be}, C_{bc}, C_{ce}) of the transistor are included with the wiring capacitances (C_{Wi}, C_{Wo}).

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2. h_{fe} (or β) Variation

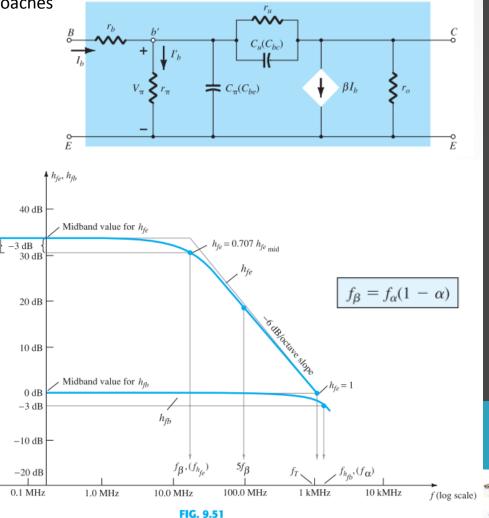
• The variation of h_{fe} (or β) with frequency approaches the following relationship:

$$h_{fe} = \frac{h_{fe_{\rm mid}}}{1 + j(f/f_{\beta})}$$

• The quantity, f_{β} , is determined by a set of parameters employed in the hybrid π model

$$f_{\beta}(\text{often appearing as } f_{h_{fe}}) = \frac{1}{2\pi r_{\pi}(C_{\pi} + C_{\mu})}$$
$$f_{\beta} = \frac{1}{h_{fe_{\text{mid}}}} \frac{1}{2\pi r_{e}(C_{\pi} + C_{\mu})}$$

- f_{β} is a function of the bias configuration.
- the small change in h_{fb} for the chosen frequency range, revealing that the common-base configuration displays improved high-frequency characteristics over the common-emitter configuration.



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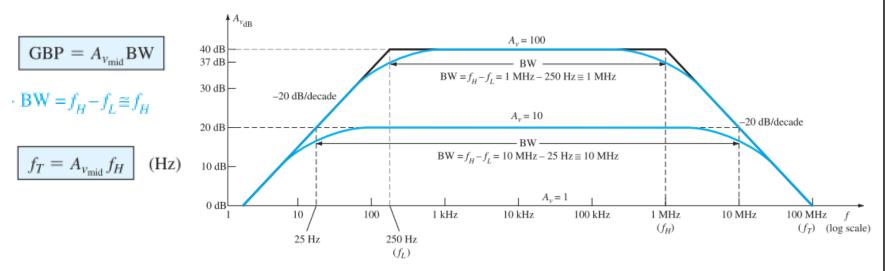
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9

h_{fe} and h_{fb} versus frequency in the high-frequency region.

Gain-Bandwidth Product

- There is a Figure of Merit applied to amplifiers called the Gain-Bandwidth Product (GBP) that is commonly used to initiate the design process of an amplifier.
- It provides important information about the relationship between the gain of the amplifier and the expected operating frequency range.



- at any level of gain the product of the two remains a constant.
- the frequency f_{τ} is called the unity-gain frequency and is always equal to the product of the midband gain of an amplifier and the bandwidth at any level of gain.



• For transistors:

 $f_T = h_{fe_{\rm mid}} f_\beta$

(Hz)

$$f_T = h_{fe_{\rm mid}} \frac{1}{2\pi h_{fe_{\rm mid}} r_e(C_\pi + C_u)}$$

$$f_T \cong \frac{1}{2\pi r_e (C_\pi + C_u)}$$



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-31

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Example

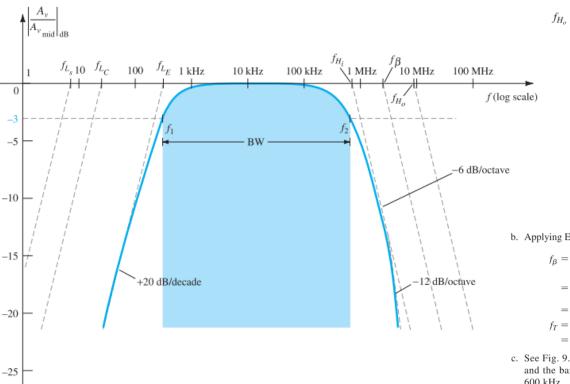
EXAMPLE 9.14 Use the network of Fig. 9.47 with the same parameters as in Example 9.12, that is,

$$\begin{aligned} R_s &= 1 \,\mathrm{k}\Omega, R_1 = 40 \,\mathrm{k}\Omega, R_2 = 10 \,\mathrm{k}\Omega, R_E = 2 \,\mathrm{k}\Omega, R_C = 4 \,\mathrm{k}\Omega, R_L = 2.2 \,\mathrm{k}\Omega\\ C_s &= 10 \,\mathrm{\mu}\mathrm{F}, C_C = 1 \,\mathrm{\mu}\mathrm{F}, C_E = 20 \,\mathrm{\mu}\mathrm{F}\\ h_{fe} &= 100, r_o = \infty \,\Omega, V_{CC} = 20 \,\mathrm{V} \end{aligned}$$

with the addition of

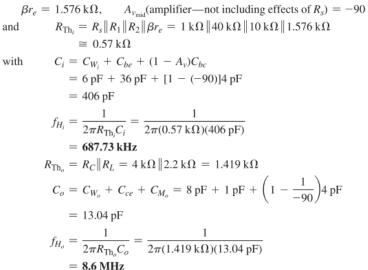
$$C_{\pi}(C_{be}) = 36 \text{ pF}, C_{u}(C_{bc}) = 4 \text{ pF}, C_{ce} = 1 \text{ pF}, C_{W_{i}} = 6 \text{ pF}, C_{W_{o}} = 8 \text{ pF}$$

- a. Determine f_{H_i} and f_{H_i} .
- b. Find f_{β} and f_{T} .
- c. Sketch the frequency response for the low- and high-frequency regions using the results of Example 9.12 and the results of parts (a) and (b).



Solution:

a. From Example 9.12:



b. Applying Eq. (9.63) gives

$$f_{\beta} = \frac{1}{2\pi h_{f_{e_{mid}}r_e}(C_{be} + C_{bc})}$$

= $\frac{1}{2\pi (100)(15.76 \ \Omega)(36 \ \text{pF} + 4 \ \text{pF})} = \frac{1}{2\pi (100)(15.76 \ \Omega)(40 \ \text{pF})}$
= **2.52 MHz**
 $f_T = h_{f_{e_{mid}}}f_{\beta} = (100)(2.52 \ \text{MHz})$
= **252 MHz**

c. See Fig. 9.54. The corner frequency f_{H_i} will determine the high cutoff frequency and the bandwidth of the amplifier. The upper cutoff frequency is very close to 600 kHz.





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Multistage Frequency Effects

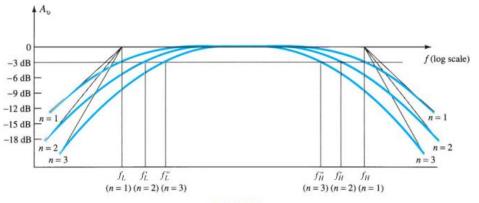


FIG. 9.58

Effect of an increased number of stages on the cutoff frequencies and the bandwidth.

$$A_{v_{\text{low, (overall)}}} = A_{v_{1_{\text{low}}}} A_{v_{2_{\text{low}}}} A_{v_{3_{\text{low}}}} \cdots A_{v_{n_{\text{low}}}}$$

but because all stages are identical, $A_{v_{1_{but}}} = A_{v_{2_{but}}} =$ etc., and

$$A_{\nu_{\text{low, (overall)}}} = (A_{\nu_{\text{low}}})^n$$
$$\frac{A_{\nu_{\text{low}}}}{A_{\nu_{\text{mid}}}} (\text{overall}) = \left(\frac{A_{\nu_{\text{low}}}}{A_{\nu_{\text{mid}}}}\right)^n = \frac{1}{(1 - jf_L/f)^n}$$

Setting the magnitude of this result equal to $1/\sqrt{2}(-3 \text{ dB level})$ results in

$$\frac{1}{\sqrt{\left[1 + (f_L/f_L')^2\right]^n}} = \frac{1}{\sqrt{2}}$$

$$\left\{ \left[1 + \left(\frac{f_L}{f_L'}\right)^{2-1}\right]^{1/2} \right\}^n = \left\{ \left[1 + \left(\frac{f_L}{f_L'}\right)^2\right]^n \right\}^{1/2} = (2)^{1/2}$$

$$\left[1 + \left(\frac{f_L}{f_L'}\right)^2\right]^n = 2$$

 $1 + \left(\frac{f_L}{f'_L}\right)^2 = 2^{1/n}$

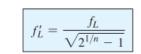
or

or

so that

with the result that

and



In a similar manner, it can be shown that for the high-frequency region,

$$f'_{H} = (\sqrt{2^{1/n} - 1})f_{H}$$

n	$\sqrt{2^{1/n}-1}$
2	0.64
3	0.51
4	0.43
5	0.39

n	$\sqrt{2^{1/n}-1}$
2	0.64
3	0.51
4	0.43
5	0.39





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Square-Wave Testing

• A sense for the frequency response of an amplifier can be determined experimentally by applying a square-wave signal to the amplifier and noting the output response.

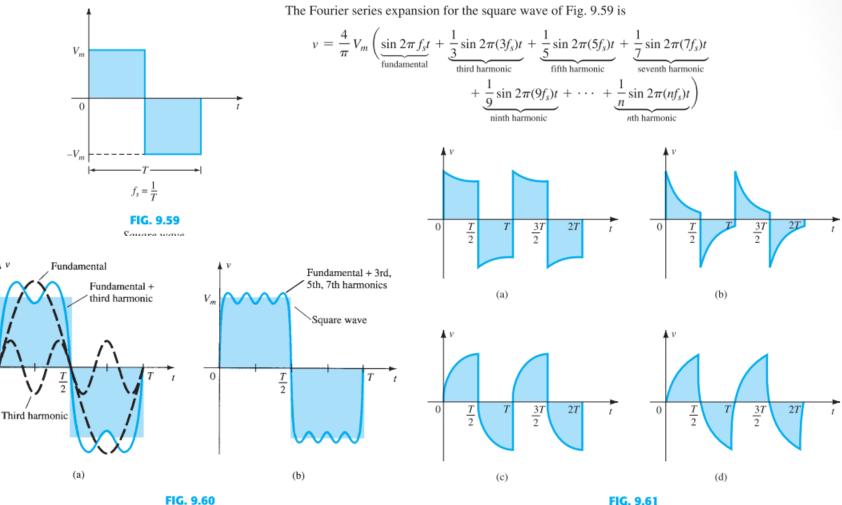


FIG. 9.60 Harmonic content of a square wave.

(a) Poor low-frequency response; (b) very poor low-frequency response; (c) poor high-frequency response; (d) very poor high-frequency response.

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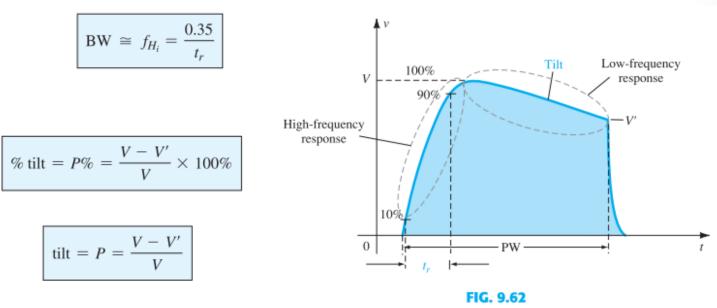
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Square-Wave Testing..

the BW of the amplifier:



The low-cutoff frequency is then determined from

$$f_{L_o} = \frac{P}{\pi} f_s$$

Defining the rise time and tilt of a square wave response.

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16

- For more details, refer to:
 - Chapter 9 at R. Boylestad, Electronic Devices and Circuit Theory, 11th edition, Prentice Hall.
- The lecture is available online at:
 - <u>http://bu.edu.eg/staff/ahmad.elbanna-courses/11966</u>
- For inquires, send to:

• <u>ahmad.elbanna@feng.bu.edu.eg</u>

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